

Application No. 10/753,269

Reply to Office Action

*SPECIFICATION AMENDMENTS*

Replace paragraph [0037] with:

The modified substrate can be planarized by a second CMP to remove the second metal overburden, e.g., to isolate and define the circuit design, and optionally to remove the exposed barrier layer if present on the modified substrate. To that end, a second chemical-mechanical polishing composition is applied to at least a portion of the modified substrate between the modified substrate and a polishing pad. The second chemical-mechanical polishing composition can be any suitable chemical-mechanical polishing composition and can be the same as or different from, preferably different from, the first chemical-mechanical polishing composition. Similarly, the polishing pad can be any suitable polishing pad and can be the same as or different from, preferably the same as, the polishing pad in the first CMP. The polishing pad then is brought into contact with the modified substrate and the second chemical-mechanical polishing composition. Once in contact, the polishing pad is moved relative to the modified substrate at a second rotational speed to polish at least a portion of the modified substrate. The second metal overburden and, if present, exposed barrier layer desirably are removed without significant dishing. While the second rotational speed can be any suitable speed, and can be the same as or different from the first and/or third rotational speeds, the second rotational speed at which the polishing pad moves relative to the substrate preferably is less than the first rotational speed.